Supporting Information

High and balanced hole and electron mobilities from ambipolar thin film transistors based-on nitrogen containing oligoacences

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Experimental Details.

General. NMR(¹H, ¹³C) spectra were recorded on a Bruker ADVANCE III 400MHz or a Varian 300MHz spectrometer at room temperature. The ¹H and ¹³C chemical shifts (δ) are reported in parts per million and the TMS was used as an internal standard. UV-Vis absorption spectra were recorded using a T6 UV-Vis spectrometer. Single crystal x-ray diffraction measurements were made on a Bruker X8 APEX diffractometer with graphite monochromated Mo-K α radiation. Fluorescence measurements were conducted using a PE LS55 fluorescence spectrometer. The electrochemical measurement was conducted using a CHI660B electrochemistry work station. Thermogravimetric analysis (TGA) was carried out on a PERKIN ELMER TGA7. A heating rate of 10 °C min⁻¹ under flowing N₂ was used with runs being conducted from room temperature to high temperature. Melting points were recorded

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(uncorrected) on a Thomas-Hoover Capillary Melting Point Apparatus. High resolution mass spectral data (HRMS) were obtained on a Bruker APEX II FT-MS and APEX QE FT-MS mass spectrometer.

FET Device Fabrication. Top contact devices were made according to a literature procedure¹. A thermally grown dry silicon dioxide layer (400nm) with a capacitance per unit area of 9.0×10^{-9} F/cm² functioned as the dielectric, while a heavily n-doped silicon substrate functioned as the gate electrode. Firstly, the substrates were cleaned by immersion in freshly prepared "piranha solution" (3:1 mixture of sulfuric acid and 30% hydrogen peroxide) for 45 minutes. Octadecyltrimethoxysilane (OTS) treatment was done by spin-coating a 3mM solution of OTS in trichloroethylene on a piranha cleaned wafer, then placing the substrate in an environment saturated with ammonia vapor for 12 hours. Shadow masks with W/L of 20 (W = 3000µm, L = 150µm) were used after the evaporation of the organic semiconductor to deposit the gold drain and source electrodes. The organic semiconductors were deposited at a rate of 0.2-0.3Å/s under a pressure of 10⁻⁶ Torr to a final thickness of 40nm as determined in-situ by a quartz crystal monitor. FET measurements were performed in the argon glove box using a Keithley 4200 semiconductor parameter analyzer.

Synthesis. Chemical reagents were purchased from Aldrich Chemical Co, TCI America, Lancaster, or Alfa Aesar and were used as received without further purification.

6,13-Anthradipyridinequinone. EtOH (50 mL) was added to 1.35 g (10 mmol) 2,3-pyridinedicarbaldehyde in a 100 mL flask and heated with stirring at 60 °C. After the dicarboxaldehyde was dissolved, 0.56 g (5.0 mmol) 1,4-cyclohexane dione was added and stirred until it was dissolved. A 15 % NaOH solution (0.5 mL) was added and the resulting precipitate was stirred for 1 h at 60 °C. The mixture was then cooled to room temperature and the brown precipitate (0.65 g, 42 %) was filtered, rinsed with water and acetone and used directly in the next reaction, M.p. > 320 °C. This compound is very insoluble, such that even proton NMR could not be measured.

1-Azapentacene-6,13-quinone. 1,4-anthraquinone (105 mg, 0.5 mmol), $\alpha,\alpha,\alpha'\alpha'$ -tetrabromo-o-xylene (317 mg, 0.75 mmol) and NaI (225 mg, 1.5 mmol) were placed in a flask under argon. Anhydrous DMF (5 ml) were added and the mixture was heated and stirred at 75 °C for 24 hrs. After cooling to room temperature, the precipitated was filtered, washed with water, CH₂Cl₂ and acetone and dried under vacuum. The 1-azapentacene-6,13-quinone was obtained as a deep yellow solid (70 mg, 45%), M.p. > 320 °C. This compound is very insoluble, such that even proton NMR could not be measured.

8,9,10,11-Tetrafluoro-1-azapentacene-6,13-quinone. 1,4-anthraquinone (105 mg, 0.5 mmol), α , α , α ' α '-tetrabromo-o -xylene (317 mg, 0.75 mmol) and NaI (225 mg, 1.5 mmol) were placed in a flask under argon. Anhydrous DMF (5 ml) were added and the mixture heated and stirred at 75 °C for 24 hrs. After cooling to room temperature, the precipitated was filtered, washed with water, CH₂Cl₂ and acetone and dried under

vacuum. The 1-azapentacene-6,13-quinone was obtained as a deep yellow solid (70 mg, 45%), M.p. > 320 °C. ¹H-NMR (300 MHz, CDCl₃) δ : 7.64-7.68 (m, 1H), 8.46-8.48 (d, 1H), 8.99 (s, 1H), 9.18-9.21 (m, 4H).

6,13-Bis-(triisopropylsilylethynyl)-anthradipyridine (1). In a oven-dried 2 necked flask with a condenser, triisopropylsilylacetylene (1.0 mL, 4.4 mmol) and dry 5 mL THF were added, then n-BuLi (1.41 mL, 2.84 M in hexanes, 4.0mmol) was added dropwise to this stirring solution at 0 °C under argon. The reaction mixture was stirred for a further 40 min at 0 °C, and then compound **6,13-anthradipyridinequinone** (310 mg, 1.0 mmol) was added to the solution, followed by 10 mL of dry THF. The mixture was heated to 60 °C for 4 hrs and then guenched with saturated ammonium chloride aqueous solution. Extraction with ethyl acetate (20 ml), washed with saturated ammonium chloride (2 \times 20 ml), dried with anhydrous Na₂SO₄. After evaporation of the solvent, the residue was filtered over silica gel using hexane/ethyl acetate (v/v, 5:1) to yield the corresponding diol (420 mg, 0.62 mmol, 62 % yeild). The crude diol was, without further characterization, dissolved in dry THF (10 mL) and SnCl₂·2H₂O (423 mg, 1.87 mmol) under argon. The mixture was heated to reflux for 2 h. After cooling to room temperature, DCM (100 mL) was added to the mixture and washed with water $(3 \times 100 \text{ mL})$. The combined organic layers were dried with anhydrous Na₂SO₄. After evaporation of the solvent, the solids were further purified by chromatography on silica gel using CH₂Cl₂ solvent. Compound 1 (166 mg, 26%) yield, two steps) was isolated as deep blue solid. M.p. 251-253 °C, ¹H-NMR (400 MHz, CDCl₃) δ: 9.55-9.59 (d, 2H), 9.29-9.35 (d, 2H), 9.01-9.02 (s, 2H), 8.27-8.30 (d,

2H), 7.32-7.34 (m, 2H), 1.35-1.37 (42H). ¹³C-NMR (100 MHz, CDCl₃) δ : 153.23, 144.69, 144.59, 136.81, 136.71, 132.60, 132.32, 130.96, 130.67, 127.85, 127.79, 127.72, 127.59, 127.49, 121.17, 119.95, 119.46, 118.91, 109.25, 108.66, 108.03, 104.24, 104.00, 103.75, 19.03, 19.01, 18.97, 11.66, 11.63, HRMS (ESI) calcd for $C_{42}H_{52}N_2Si_2$ (MH⁺) 641.3742; found: 641.3750.

6,13-Bis-(triisopropylsilylethynyl)-1-azapentacene (2). In a oven-dried 2-necked flask with a condenser, triisopropylsilylacetylene (0.3 mL, 1.32 mmol) and dry 4 mL THF were added, then n-BuLi (0.42 mL, 2.82 M in hexanes, 1.2mmol) was added dropwise to this stirring solution at 0 °C under argon. The reaction mixture was allowed to warm to room temperature and stirred for a further 40 min, and then 1-azapentacene-6,13-quinone (62 mg, 0.2 mmol) was added to the solution, followed by 6 mL of dry THF. The mixture was heated to 60 °C for 4 hrs and then quenched with saturated ammonium chloride aqueous solution. Extraction with ethyl acetate (10 ml) was washed with saturated ammonium chloride (2×10 ml), and dried with anhydrous Na₂SO₄. After evaporation of the solvent, the residue was filtered over silica gel using hexane/ethyl acetate (v/v, 5:1) to yield the corresponding diol (84 mg, 0.12 mmol, 62 % yeild). The crude diol was, without further characterization, dissolved in THF (5 mL) and SnCl₂·2H₂O (81 mg, 0.36 mmol) under argon. The mixture was heated to reflux for 6 h. After cooling to room temperature, ethyl ether (100 mL) was added to the mixture and washed with water (3 \times 100 mL). The combined organic layers were dried with anhydrous Na₂SO₄. After evaporation of the solvent, the solids were further purified by chromatography on silica gel using a

hexane/CH₂Cl₂ (v/v, 1:1) solvent mixture. Compound **2** (31 mg, 24% yield, two steps) was isolated as deep blue solid. M.p. 248–250 °C, ¹H-NMR (400 MHz, CDCl₃) δ : 9.55 (s, 1H), 9.38(s, 1H), 9.29-9.32 (d, 2H), 9.00-9.01 (d, 1H), 8.28-8.31 (d, 1H), 7.97-8.00 (dd, 2H), 7.43-7.45 (dd, 2H), 7.26-7.34 (m, 1H), 1.36-1.38 (42H). ¹³C-NMR (100 MHz, CDCl₃) δ : 152.83, 132.62, 132.54, 132.19, 131.11, 130.82, 130.55, 128.71, 128.64, 127.50, 126.58, 126.38, 126.31, 120.87, 119.24, 118.71, 108.34, 107.70, 104.47, 104.21, 19.04, 18.99, 11.69, HRMS (ESI) calcd for C₄₃H₅₃NSi₂ (MH⁺) 640.3795; found: 641.3789.

8,9,10,11-Tetrafluoro-6,13-bis-(triisopropylsilylethynyl)-1-azapentacene (3). 3 was prepared by the reaction of triisopropylsilylacetylene (0.3ml, 1.32 mmol) and **8,9,10,11-tetrafluoro-1-azapentacene-6,13-quinone** (76mg, 0.2 mmol). With the similar procedure as the synthesis of compound **2**, **3** was obtained as a deep blue solid (36 mg, 25% yield). M.P. 304–306 °C, ¹H-NMR (400 MHz, CDCl₃) δ : 9.61 (s, 1H), 9.55-9.57 (d, 2H), 9.29 (s, 1H), 9.04-9.05(d, 1H), 8.31-8.32 (d, 1H), 7.35-7.38 (dd, 1H), 1.36-1.37 (d, 42H). ¹³C-NMR (100 MHz, CDCl₃) δ : 153.50, 144.83, 136.81, 132.58, 130.89, 130.63, 130.37, 128.15, 127.86, 127.75, 121.45, 120.40, 119.98, 119.67, 119.48, 109.82, 109.20, 103.51, 103.30, 18.94, 18.90, 11.57, HRMS (MALDI) calcd for C₈₆H₉₉N₂Si₄F₈ (2MH⁺) 1423.6758; found: 1423.6752.

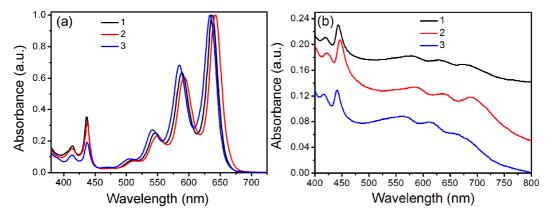


Figure 1. UV-Vis of 1 (black line), 2 (red line) and 3 (blue line) in a dilute toluene solution (left) and a 40nm thin film on quartz (right) made under device conditions.

Cyclic voltammograms.

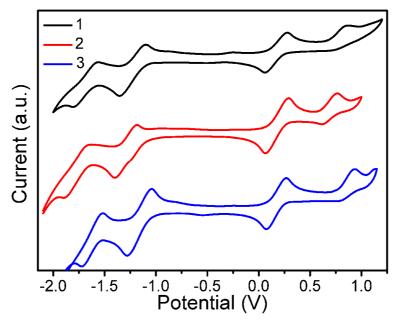


Figure 2. Cyclic voltammograms of compound 1, 2 and 3 as solutions in CH_2Cl_2 solution (0.1 M Bu₄NBF₄ electrolyte), Pt electrode. Scan rate: 100 mV/s. Fc/Fc⁺ (-4.8 eV to vacuum) as internal reference.

FET characteristics.

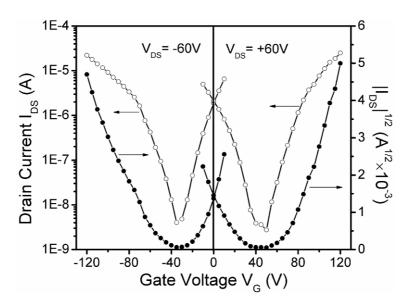


Figure 3. Typical transfer curves for **1** deposited at 80°C on OTS-treated SiO₂ for L=150 μ m, W/L=20. The gate voltage ranges from -120 to 120 V.

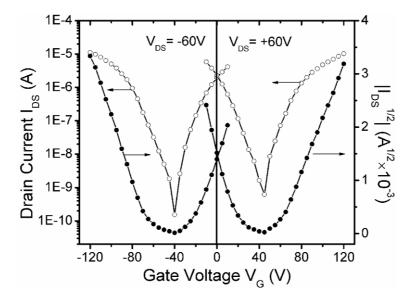


Figure 4. Typical transfer curves for **3** deposited at 80°C on OTS-treated SiO₂ for L=150 μ m, W/L=20. The gate voltage ranges from -120 to 120 V.

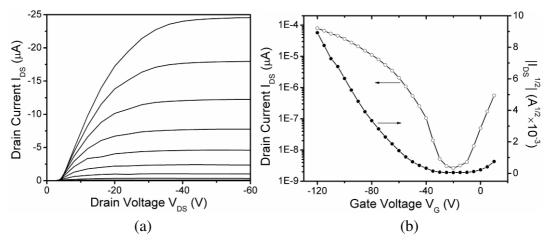


Figure 5. Typical output(a) and transfer(b) curves for **2** deposited at 80°C on OTS-treated SiO₂ for L=150 μ m, W/L=20. The gate voltage ranges from -120 to 10 V.

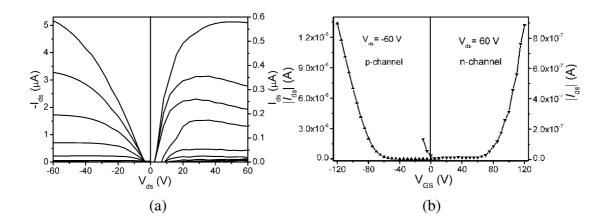
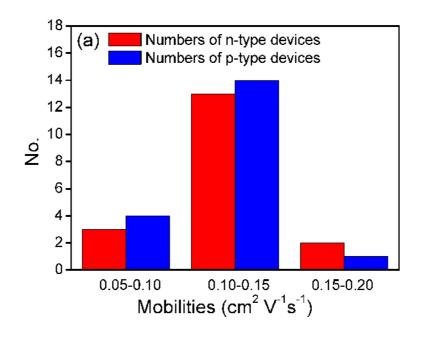


Figure 6. Typical output(a) and transfer(b) curves for **2** deposited at 80°C on OTS-treated SiO₂ with Ag as electrode material for L=150 μ m, W/L=20. The gate voltage ranges from -120 to 10 V.



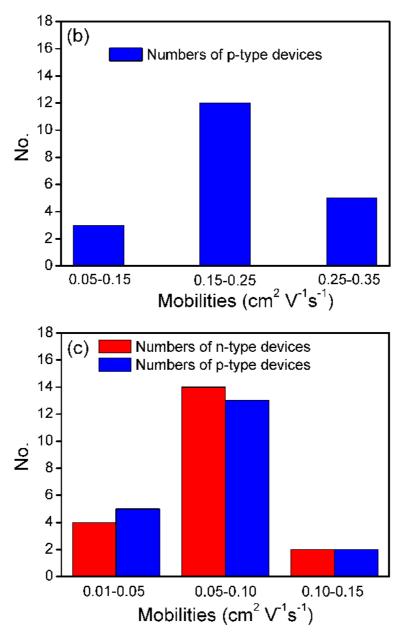


Figure 7. Statistical results of thin film transistor mobilities of compound 1 (a), 2 (b) and 3 (c). The organic layers were deposited at 80 $^{\circ}$ C.

AFM images. An Agilent 5500 scanning probe microscope was used to perform tapping mode AFM on the samples by a silicon tip with spring constant of 130N/m. Picoview software was used to process the raw AFM images.

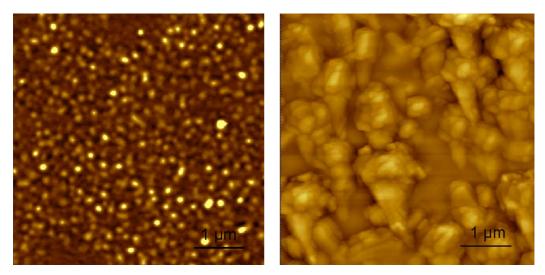


Figure 8. AFM images of 1 on OTS treated SiO_2 at substrate temperature of R.T. (left) and 80°C (right).

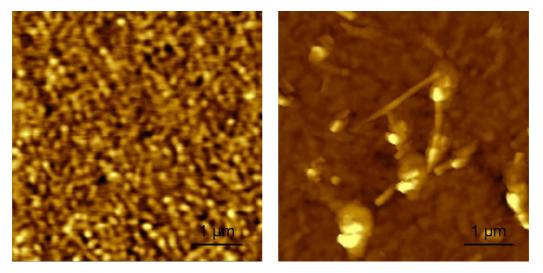


Figure 9. AFM images of 2 on OTS treated SiO_2 at substrate temperature of R.T. (left) and $80^{\circ}C$ (right).

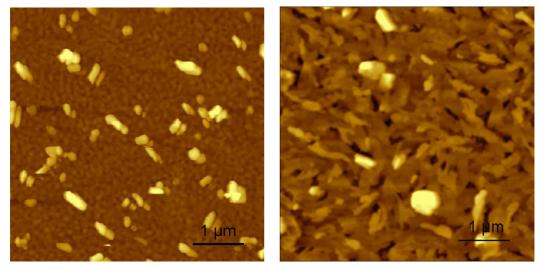


Figure 10. AFM images of **3** on OTS treated SiO_2 at substrate temperature of R.T. (left) and $80^{\circ}C$ (right).

Reference

(1) Locklin, J.; Roberts, M. E.; Mannsfeld, S. C. B.; Bao, Z. Journal of Macromolecular Science, Part C: Polymer Reviews 2006, 46, 79-101.